

IN THE CLAIMS:

This listing of the claims will replace all prior listings, and versions, of the claims.

1. (Currently amended) A lithographic projection apparatus, comprising:
  - a radiation system configured to provide a ~~projection~~ beam of radiation, the ~~projection~~ beam being patterned by a patterning device;
  - a substrate table configured to hold a substrate;
  - a projection system configured to project the patterned beam onto a target portion of the substrate;
  - a processing unit configured to process the substrate at least one of before and after the substrate has been exposed to the ~~projection~~ beam of radiation;
  - a transport unit configured to transport the substrate between the substrate table and the processing unit; and
  - a contamination control device configured to control the partial pressure of H<sub>2</sub>O in the transport unit to be less than  $1 \times 10^{-2}$  mbar, the partial pressure of hydrocarbons in the transport unit to be less than  $1 \times 10^{-4}$  mbar, and the partial pressure of amine bases in the transport unit to be less than  $1 \times 10^{-6}$  mbar.
2. (Original) A lithographic projection apparatus according to claim 1, wherein the contamination control device is configured to control the partial pressure of contaminants in the transport unit to be less than 1 mbar.
3. (Original) A lithographic projection apparatus according to claim 1, wherein contamination control device is configured to control the partial pressure of H<sub>2</sub>O in the transport unit to be less than  $1 \times 10^{-5}$  mbar, the partial pressure of hydrocarbons in the transport unit to be less than  $1 \times 10^{-7}$  mbar, and the partial pressure of amine bases in the transport unit to be less than  $1 \times 10^{-7}$  mbar.
4. (Original) A lithographic projection apparatus according to claim 1, wherein the contamination control device substantially evacuates the transport unit.

5. (Original) A lithographic projection apparatus according to claim 4, wherein at least one of a space surrounding the substrate table and a space surrounding the processing unit is substantially evacuated.
6. (Original) A lithographic projection apparatus according to claim 1, wherein the contamination control device comprises a gas supply configured to supply a substantially contaminant-free gas to fill the transport unit.
7. (Original) A lithographic projection apparatus according to claim 6, wherein the substantially contaminant-free gas is one of substantially pure nitrogen and synthetic air.
8. (Currently amended) A lithographic projection apparatus according to claim 1, wherein the ~~projection~~ beam of radiation is EUV radiation.
9. (Original) A lithographic projection apparatus according to claim 1, wherein the processing unit is configured to at least one of:
  - apply a layer of resist to the substrate;
  - bake the substrate to process the resist;
  - cool the substrate after it has been baked; and
  - develop the substrate with the resist.
10. (Original) A lithographic projection apparatus according to claim 1, wherein the transport unit is configured to at least one of:
  - bake the substrate to process the resist; and
  - cool the substrate after it has been baked.
11. (Currently amended) A device manufacturing method, comprising:
  - ~~providing a substrate that is at least partially covered by a layer of radiation-sensitive material;~~
  - projecting a patterned beam of radiation onto a target portion of ~~[[the]]~~ a layer of radiation-sensitive material at least partially covering a substrate; and
  - transporting the substrate in a transport unit between a substrate table and a processing unit configured to process the substrate at least one of before and after it has been

exposed by the patterned beam of radiation, wherein a partial pressure of H<sub>2</sub>O in the transport unit is less than  $1 \times 10^{-2}$  mbar, a partial pressure of hydrocarbons in the transport unit is less than  $1 \times 10^{-4}$  mbar, and a partial pressure of amine bases in the transport unit is less than  $1 \times 10^{-6}$  mbar.

12. (Original) A device manufacturing method according to claim 11, wherein a partial pressure of contaminants in the transport unit is less than 1 mbar.

13. (Original) A device manufacturing method according to claim 11, the partial pressure of H<sub>2</sub>O in the transport unit is less than  $1 \times 10^{-5}$  mbar, the partial pressure of hydrocarbons in the transport unit is less than  $1 \times 10^{-7}$  mbar, and the partial pressure of amine bases in the transport unit is less than  $1 \times 10^{-7}$  mbar.

14. (Original) A device manufacturing method according to claim 11, further comprising substantially evacuating the transport unit.

15. (Original) A device manufacturing method according to claim 11, further comprising filling the transport unit with a substantially contaminant-free gas.

16. (Original) A device manufacturing method according to claim 15, wherein the substantially contaminant-free gas is one of substantially pure nitrogen and synthetic air.

17. (Original) A device manufacturing method according to claim 11, further comprising at least one of:

- applying a layer of resist to the substrate;
- baking the substrate to process the resist;
- cooling the substrate after it has been baked; and
- developing the substrate with the resist.

18. (Currently amended) A device manufacturing method according to claim 11, wherein the ~~projection~~ beam of radiation is EUV radiation.

19. (Original) A device manufactured by the method of claim 11.

20. (New) A transport unit configured to transport a substrate between a lithographic projection apparatus and a processing unit, wherein the transport unit comprises a contamination control device configured to control the partial pressure of H<sub>2</sub>O in the transport unit to be less than  $1 \times 10^{-2}$  mbar, the partial pressure of hydrocarbons in the transport unit to be less than  $1 \times 10^{-4}$  mbar, and the partial pressure of amine bases in the transport unit to be less than  $1 \times 10^{-6}$  mbar.
21. (New) A transport unit according to claim 20, wherein the contamination control device is configured to control the partial pressure of contaminants in the transport unit to be less than 1 mbar.
22. (New) A transport unit according to claim 20, wherein contamination control device is configured to control the partial pressure of H<sub>2</sub>O in the transport unit to be less than  $1 \times 10^{-5}$  mbar, the partial pressure of hydrocarbons in the transport unit to be less than  $1 \times 10^{-7}$  mbar, and the partial pressure of amine bases in the transport unit to be less than  $1 \times 10^{-7}$  mbar.
23. (New) A transport unit according to claim 20, wherein the contamination control device substantially evacuates the transport unit.
24. (New) A transport unit according to claim 20, wherein the contamination control device comprises a gas supply configured to supply a substantially contaminant-free gas to fill the transport unit.
25. (New) A transport unit according to claim 24, wherein the substantially contaminant-free gas is one of substantially pure nitrogen and synthetic air.